



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

ATP216 — General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS(on)1}=17\text{m}\Omega(\text{typ.})$
- 1.8V drive
- Slim package
- Halogen free compliance

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

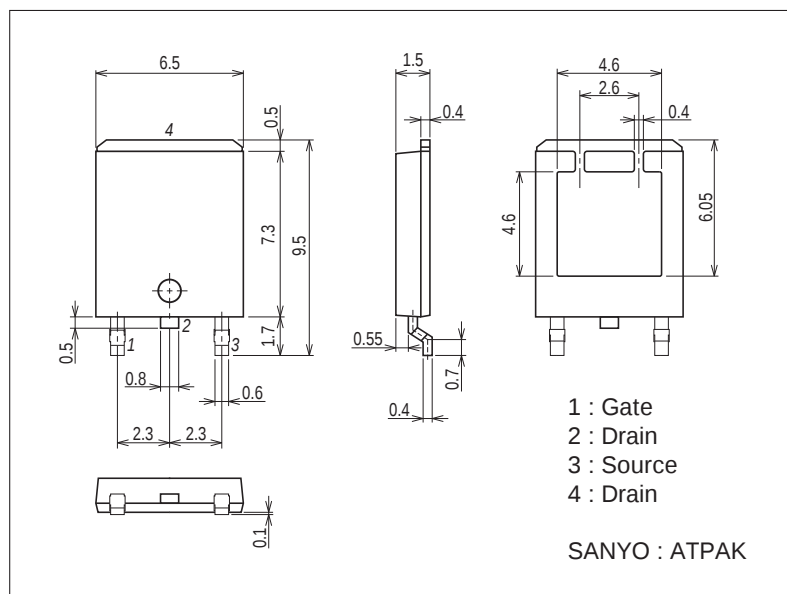
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		50	V
Gate-to-Source Voltage	V_{GS}		± 10	V
Drain Current (DC)	I_D		35	A
Drain Current ($PW \leq 10\mu\text{s}$)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	105	A
Allowable Power Dissipation	P_D	$T_c=25^\circ\text{C}$	40	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
Avalanche Energy (Single Pulse) *1	E_{AS}		40	mJ
Avalanche Current *2	I_{AV}		17.5	A

Note : *1 $V_{DD}=10\text{V}$, $L=100\mu\text{H}$, $I_{AV}=18\text{A}$ *2 $L \leq 100\mu\text{H}$, Single pulse

Package Dimensions

unit : mm (typ)

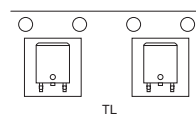
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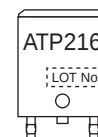
Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

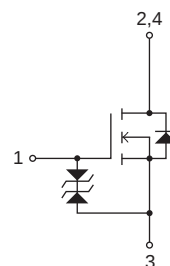
Packing Type: TL



Marking



Electrical Connection

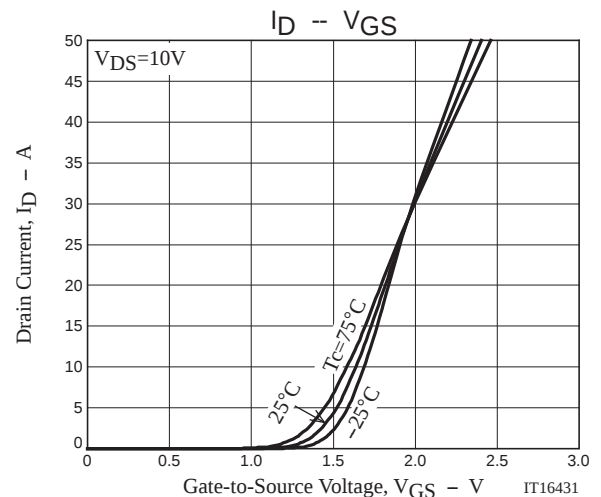
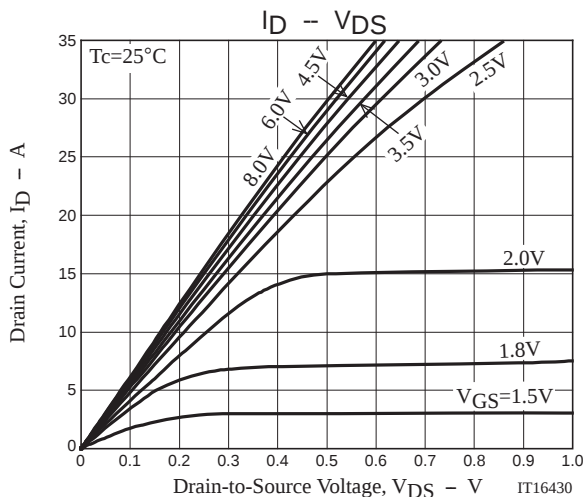
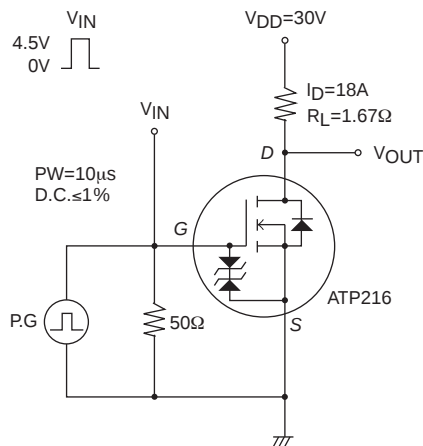


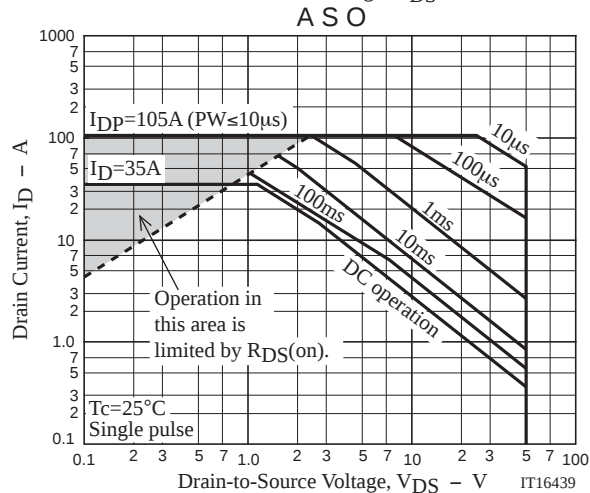
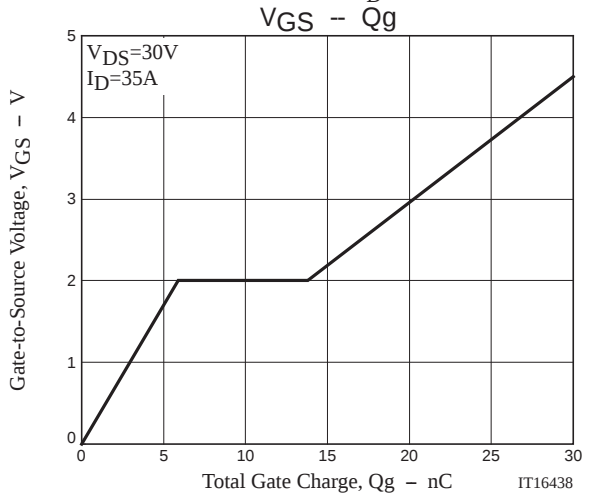
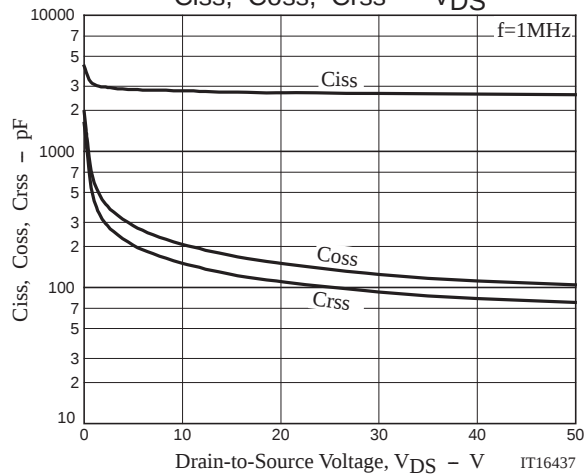
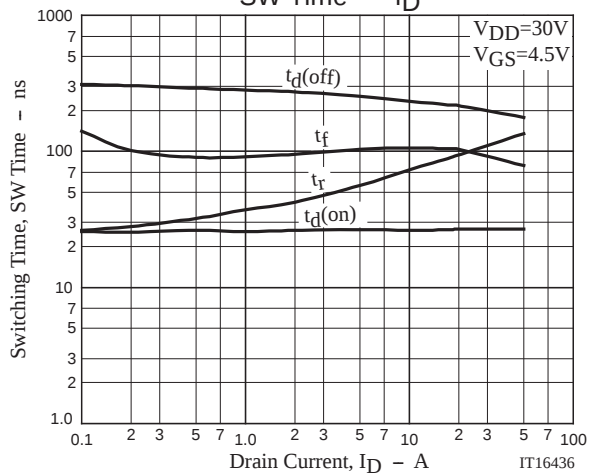
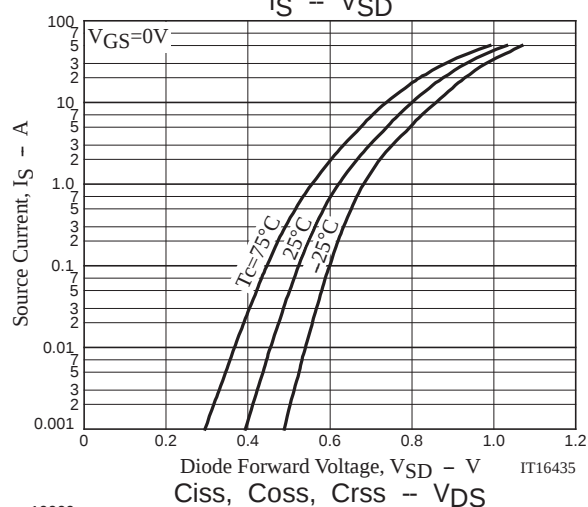
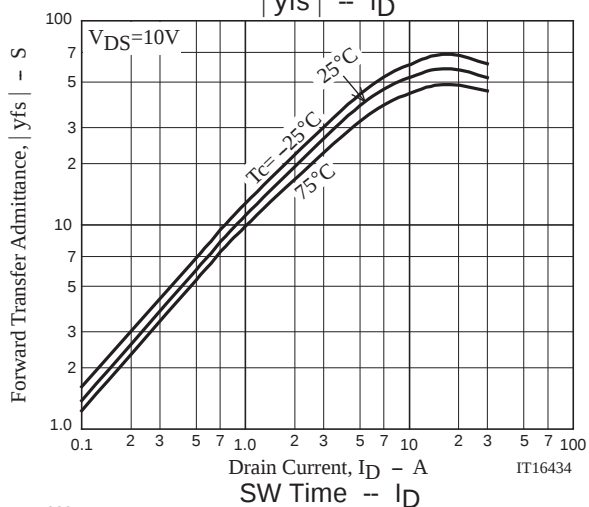
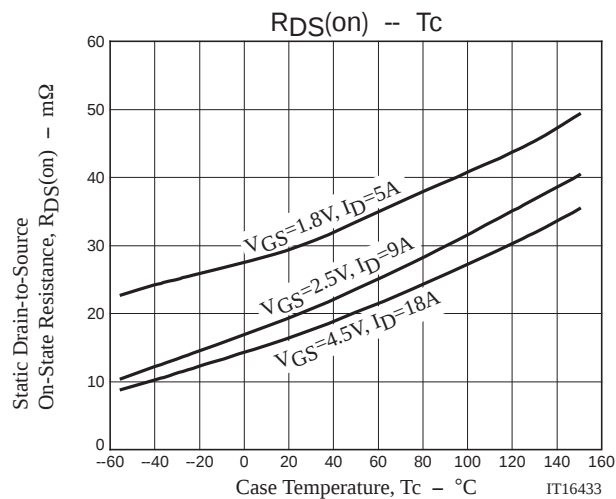
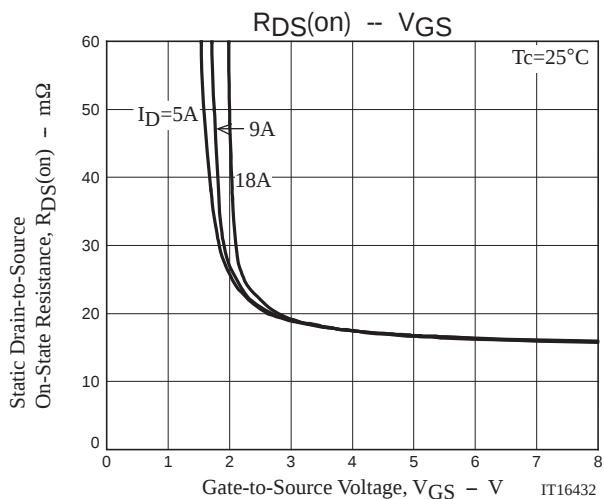
ATP216

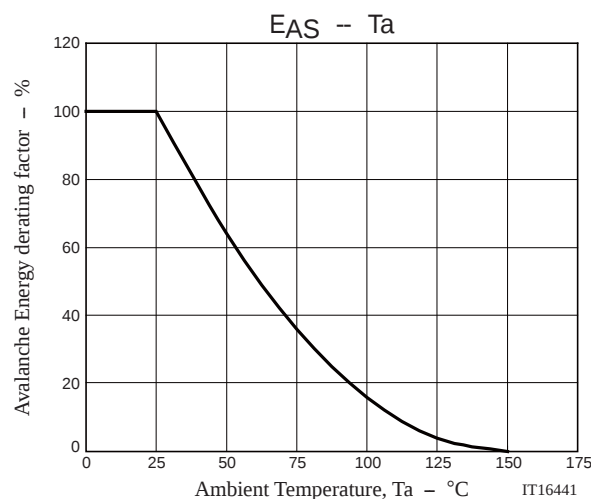
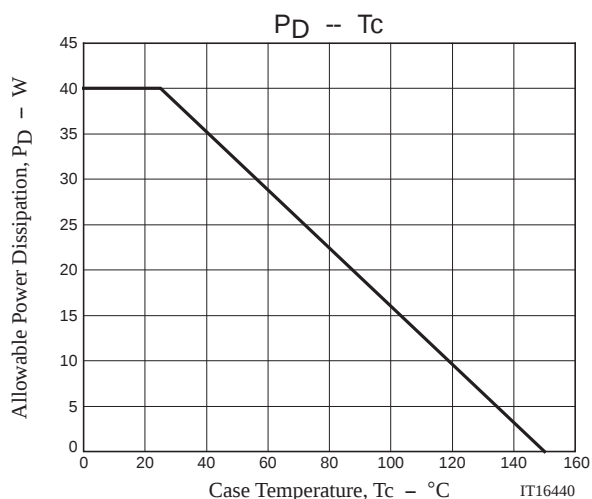
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	50			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=50V, V_{GS}=0V$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	0.4		1.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=18A$		58		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=18A, V_{GS}=4.5V$		17	23	$m\Omega$
	$R_{DS(on)2}$	$I_D=9A, V_{GS}=2.5V$		20	28	$m\Omega$
	$R_{DS(on)3}$	$I_D=5A, V_{GS}=1.8V$		30	45	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=20V, f=1MHz$		2700		pF
Output Capacitance	C_{oss}	$V_{DS}=20V, f=1MHz$		150		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=20V, f=1MHz$		110		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		27		ns
Rise Time	t_r	See specified Test Circuit.		90		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		220		ns
Fall Time	t_f	See specified Test Circuit.		105		ns
Total Gate Charge	Q_g	$V_{DS}=30V, V_{GS}=4.5V, I_D=35A$		30		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=30V, V_{GS}=4.5V, I_D=35A$		5.9		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=30V, V_{GS}=4.5V, I_D=35A$		7.9		nC
Diode Forward Voltage	V_{SD}	$I_S=35A, V_{GS}=0V$		0.96	1.2	V

Switching Time Test Circuit







Note on usage : Since the ATP216 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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